

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_b
100V	29mΩ@10V	27A
	47mΩ@4.5V	

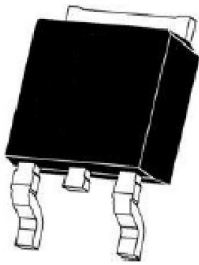
Feature

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery
- Suffix "-Q1" for AEC-Q101

Application

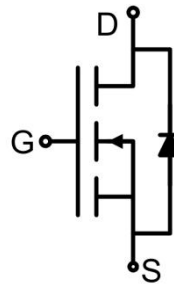
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply
- DC-DC convertor

Package

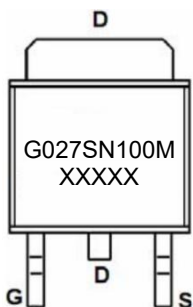


TO-252AB

Circuit diagram



Marking



Absolute maximum ratings($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_C=25^\circ\text{C}$)	I_D	27	A
Continuous Drain Current ($T_C=100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	19	A
Pulsed Drain Current ¹⁾	I_{DM}	80	A
Single Pulse Avalanche Energy ²⁾	E_{AS}	27.5	mJ
Power Dissipation ³⁾ ($T_C=25^\circ\text{C}$)	P_D	50	W
Thermal Resistance Junction to Case	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Operating Junction Temperature	T_J	-55 ~ +175	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 ~ +175	$^\circ\text{C}$

Electrical characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	100			V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=100\text{V}, V_{GS}=0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{DS}=0\text{V}, V_{GS}=\pm 20\text{V}$			± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	1	1.7	2.5	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS}=10\text{V}, I_D=20\text{A}$		22	29	m Ω
		$V_{GS}=4.5\text{V}, I_D=20\text{A}$		32	47	
Dynamic characteristics⁴⁾						
Input Capacitance	C_{iss}	$V_{DS}=50\text{V}, V_{GS}=0\text{V}, f=1\text{MHz}$		515		pF
Output Capacitance	C_{oss}			120		
Reverse Transfer Capacitance	C_{rss}			6		
Total Gate Charge	Q_g	$V_{DS}=50\text{V}, V_{GS}=10\text{V}, I_D=15\text{A}$		12.7		nC
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			5.5		
Turn-on delay time	$t_{d(on)}$	$V_{DS}=50\text{V}, V_{GS}=10\text{V}, I_D=15\text{A}$ $R_G=2.2\Omega$		5.3		nS
Turn-on rise time	t_r			36		
Turn-off delay time	$t_{d(off)}$			13		
Turn-off fall time	t_f			2.4		
Source-Drain Diode characteristics						
Diode Continuous Current	I_S				27	A
Diode Forward voltage	V_{SD}	$V_{GS}=0\text{V}, I_S=20\text{A}$			1.2	V
Reverse recover time	T_{rr}	$I_F=15\text{A}, di/dt=-100\text{A}/\mu\text{s}$		67.5		nS
Reverse recovery charge	Q_{rr}			40.7		nC

Notes:

- 1) Repetitive rating; pulse width limited by max. junction temperature.
- 2) $T_J=25^\circ\text{C}, V_G=10\text{V}, R_G=25\Omega, L=0.5\text{mH}, I_{AS}=10.5\text{A}$.
- 3) P_D is based on max. junction temperature, using junction-case thermal resistance.
- 4) Guaranteed by design, not subject to production testing.

Typical Characteristics

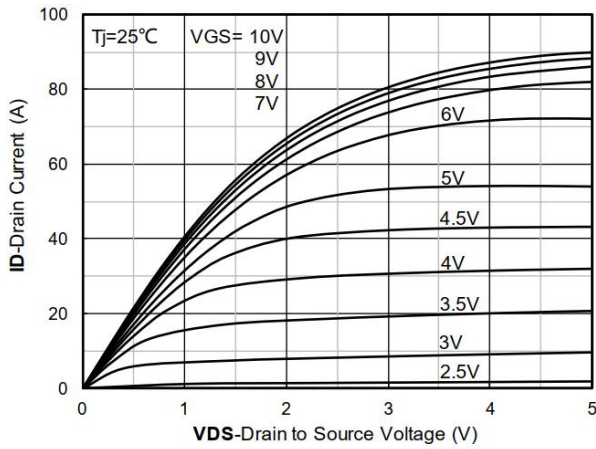


Figure 1. Output Characteristics

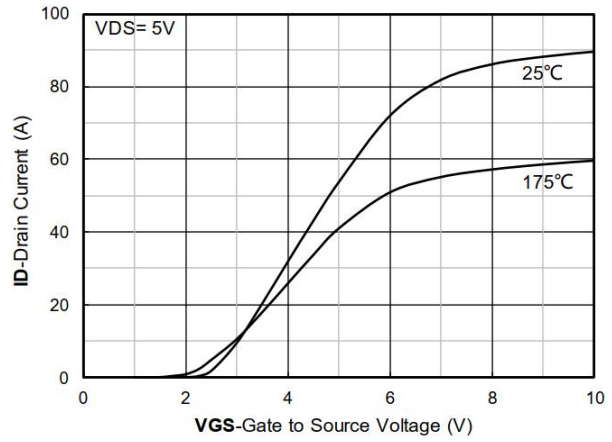


Figure 2. Transfer Characteristics

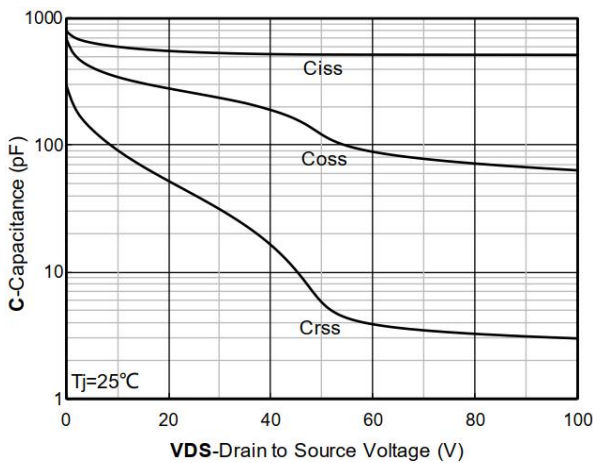


Figure 3. Capacitance Characteristics

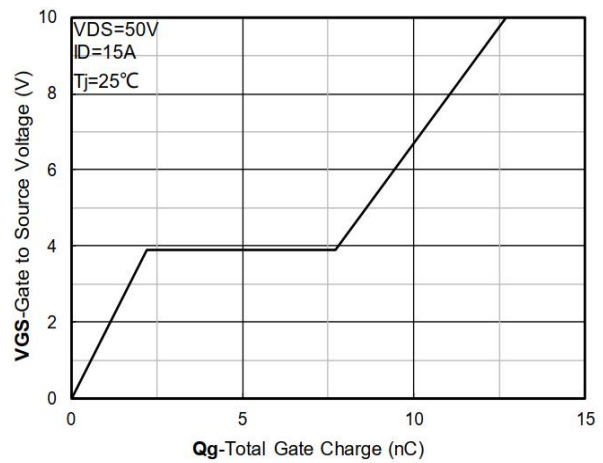


Figure 4. Gate Charge

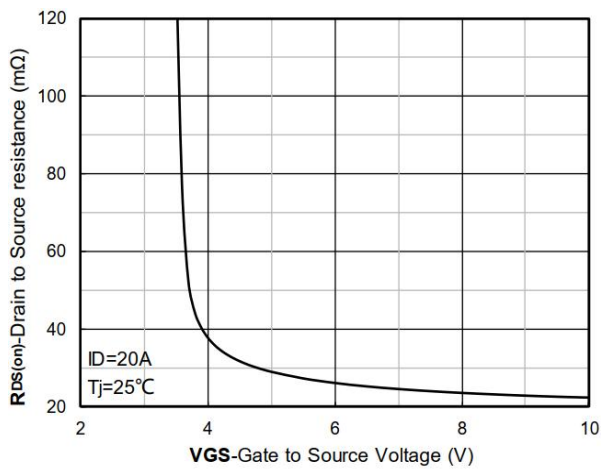


Figure 5. On-Resistance vs Gate to Source Voltage

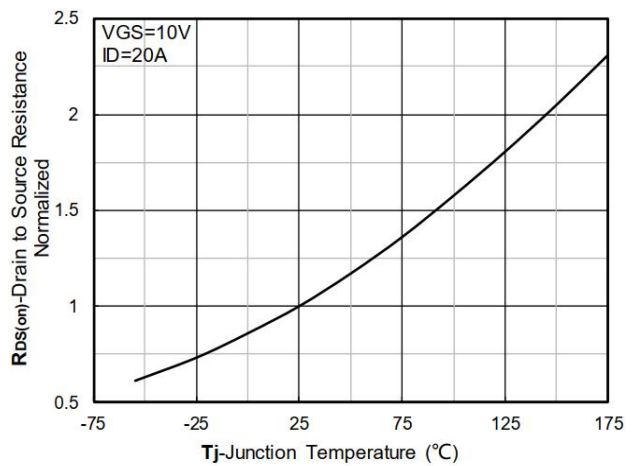


Figure 6. Normalized On-Resistance

Typical Characteristics

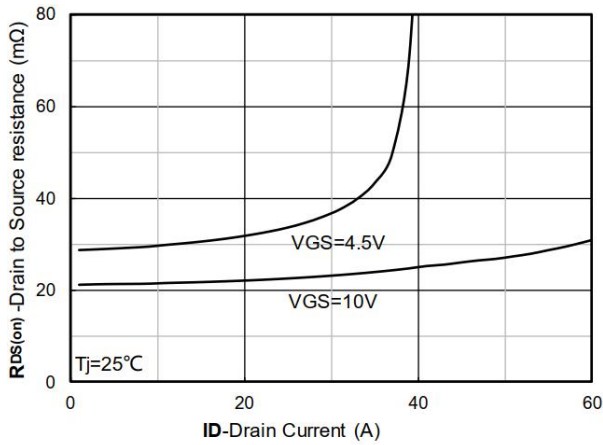


Figure 7. RDS(on) VS Drain Current

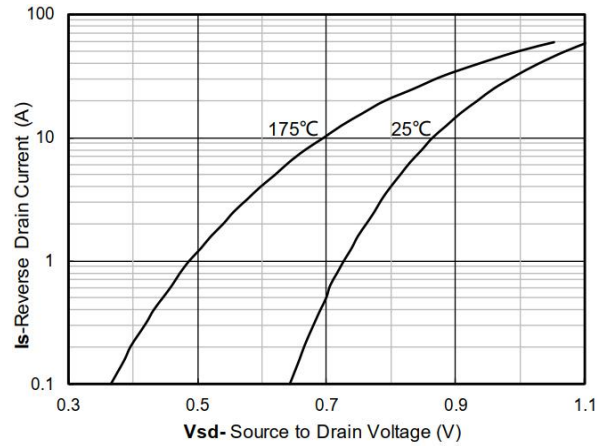


Figure 8. Forward characteristics of reverse diode

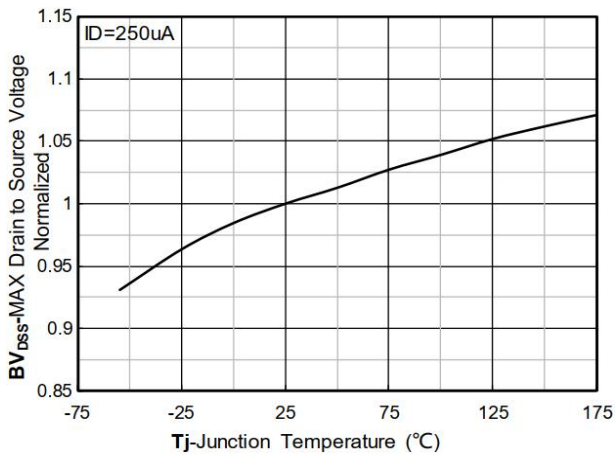


Figure 9. Normalized breakdown voltage

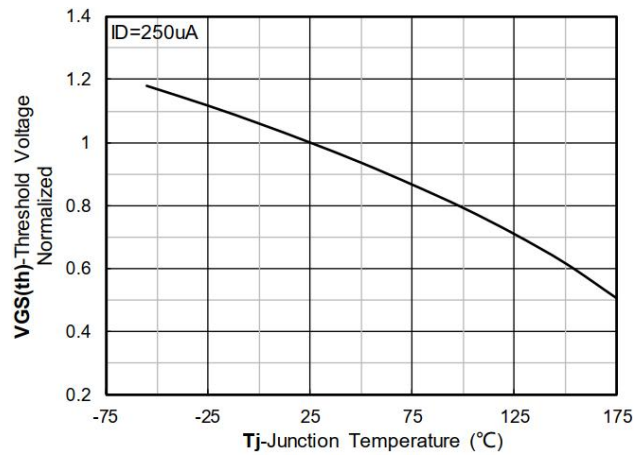


Figure 10. Normalized Threshold voltage

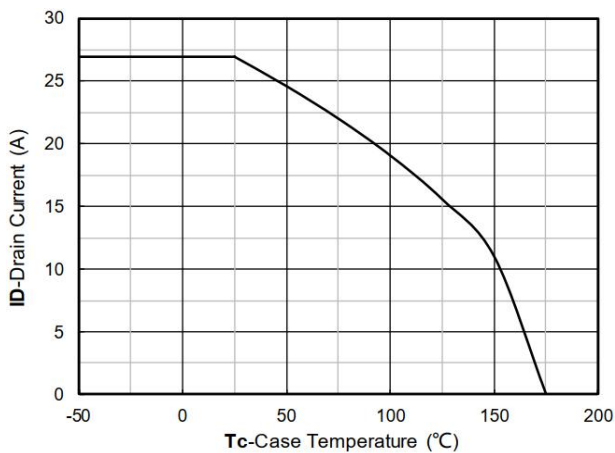


Figure 11. Current dissipation

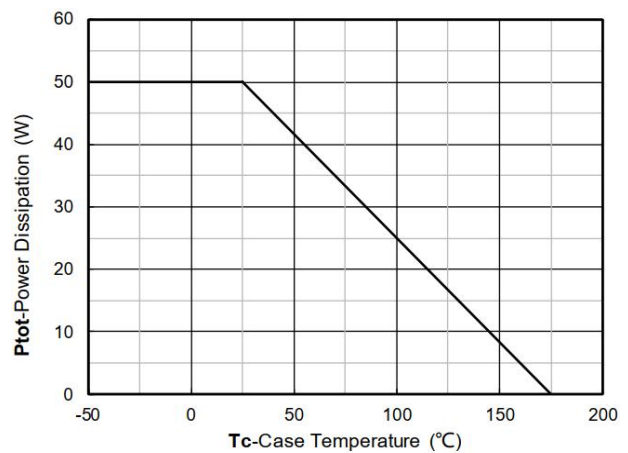


Figure 12. Power dissipation

Typical Characteristics

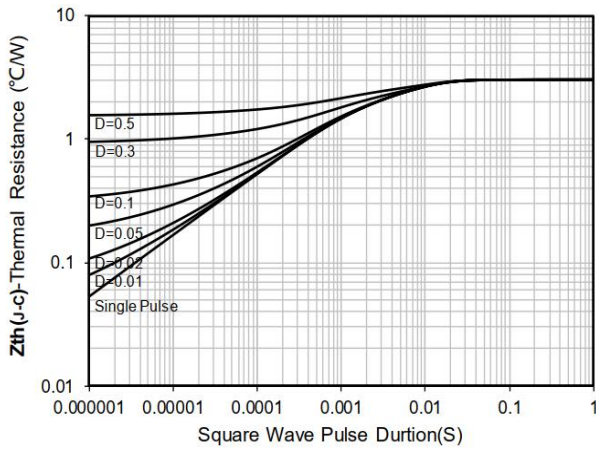


Figure 13. Maximum Transient Thermal Impedance

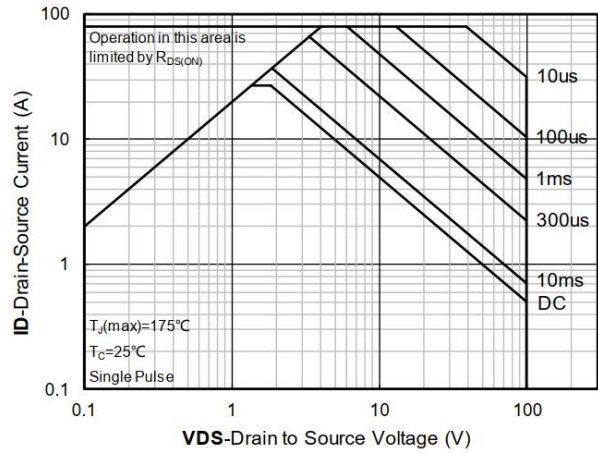
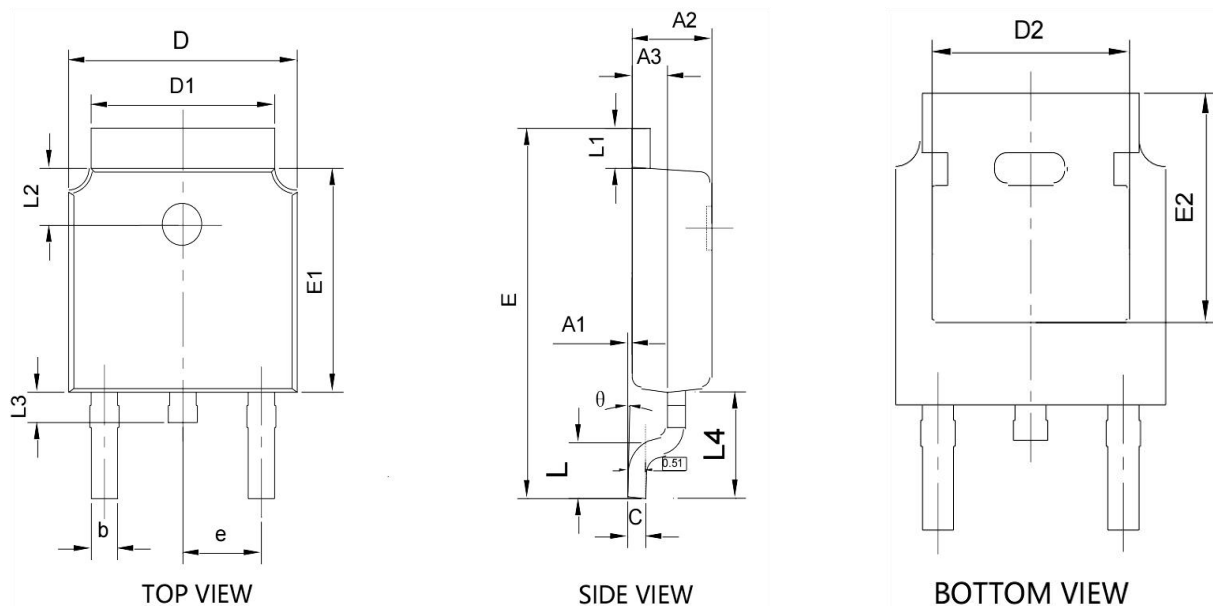


Figure 14. Safe Operation Area

TO-252AB Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A1	0.000	0.200	0.000	0.008
A2	2.200	2.400	0.087	0.094
A3	0.900	1.100	0.035	0.043
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.150	5.450	0.203	0.215
D2	4.600	4.950	0.181	0.195
E	9.900	10.300	0.390	0.406
E1	6.000	6.200	0.236	0.244
E2	5.150	5.450	0.203	0.215
e	2.286 BSC.		0.090 BSC.	
L	1.250	1.750	0.049	0.069
L1	0.900	1.270	0.035	0.050
L2	1.400	1.900	0.055	0.075
L3	0.600	1.000	0.024	0.039
L4	2.900 REF.		0.114 REF.	
θ	0°	10°	0°	10°